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ABSTRACT

AMBIPOLAR, LIGHT-EMITTING FIELD-EFFECT TRANSISTORS

An ambipolar, light-emitting transistor comprising an organic semiconductive layer in contact with an electron injecting electrode and a hole injecting electrode separated by a distance L defining the channel length of the transistor, in which the zone of the organic semiconductive layer from which the light is emitted is located more than L/10 away from both the electron as well as the hole injecting electrode.